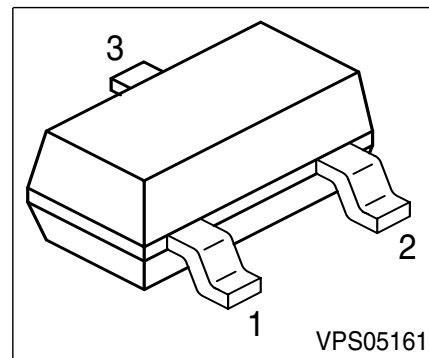
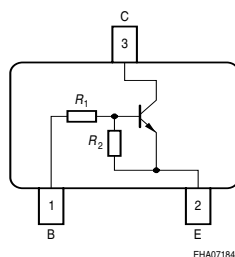


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=1k\Omega$, $R_2=10k\Omega$)



Type	Marking	Pin Configuration			Package
BCR523	XGs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Input on Voltage	$V_{i(on)}$	12	
DC collector current	I_C	500	mA
Total power dissipation, $T_S = 79^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤ 215	K/W
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¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

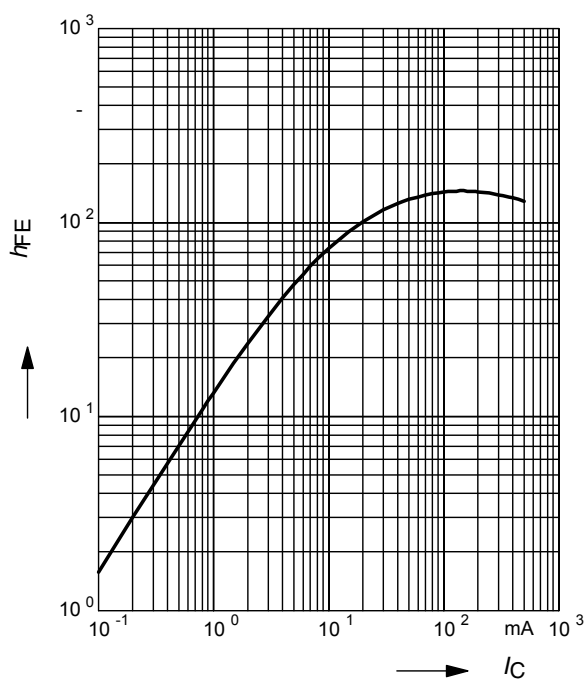
Electrical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}, I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}, I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector cutoff current $V_{\text{CB}} = 40\ \text{V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter cutoff current $V_{\text{EB}} = 5\ \text{V}, I_C = 0$	I_{EBO}	-	-	0.72	mA
DC current gain 1) $I_C = 50\ \text{mA}, V_{\text{CE}} = 5\ \text{V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage1) $I_C = 50\ \text{mA}, I_B = 2.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}, V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0.3	-	1	
Input on Voltage $I_C = 10\ \text{mA}, V_{\text{CE}} = 0.3\ \text{V}$	$V_{\text{i(on)}}$	0.4	-	1.4	
Input resistor	R_1	0.7	1	1.3	kΩ
Resistor ratio	R_1/R_2	0.09	0.1	0.11	-
AC Characteristics					
Transition frequency $I_C = 50\ \text{mA}, V_{\text{CE}} = 5\ \text{V}, f = 100\ \text{MHz}$	f_{T}	-	100	-	MHz

 1) Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

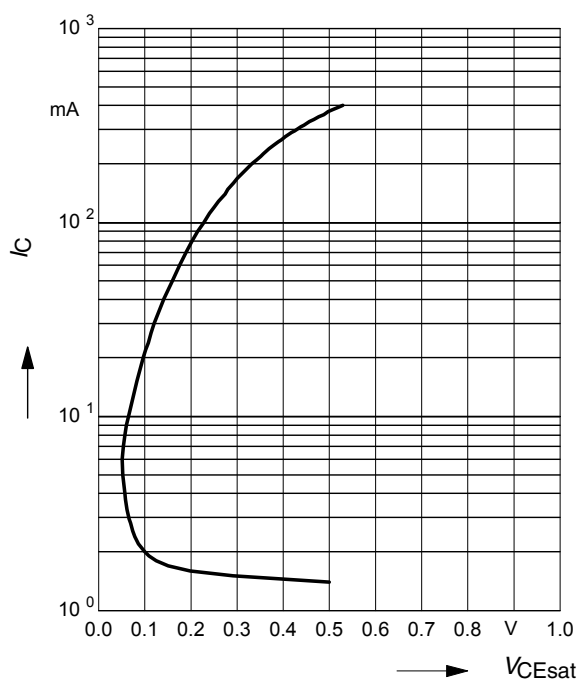
DC Current Gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



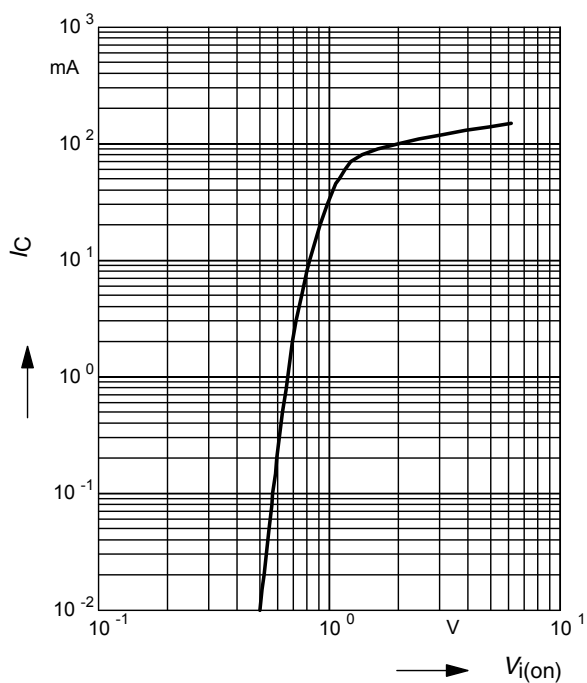
Collector-Emitter Saturation Voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



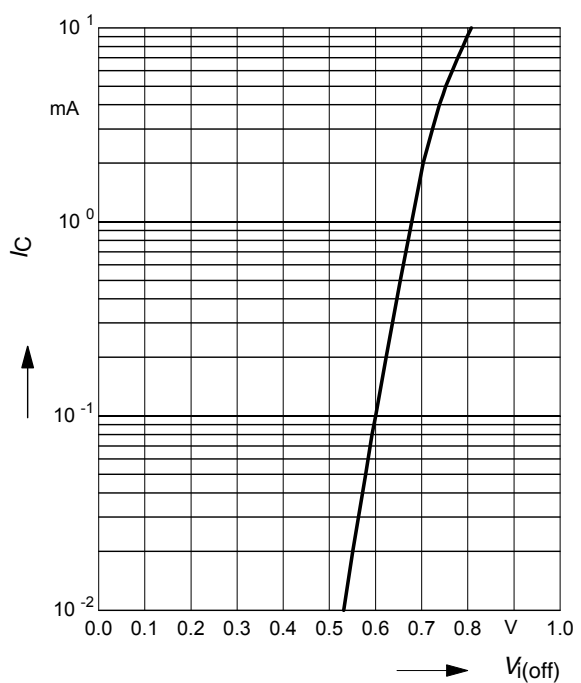
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)

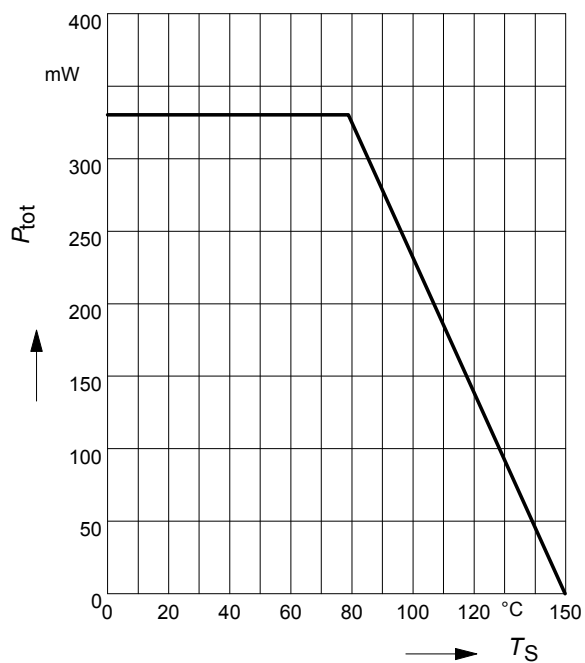


Input off voltage $V_{i(off)} = f(I_C)$

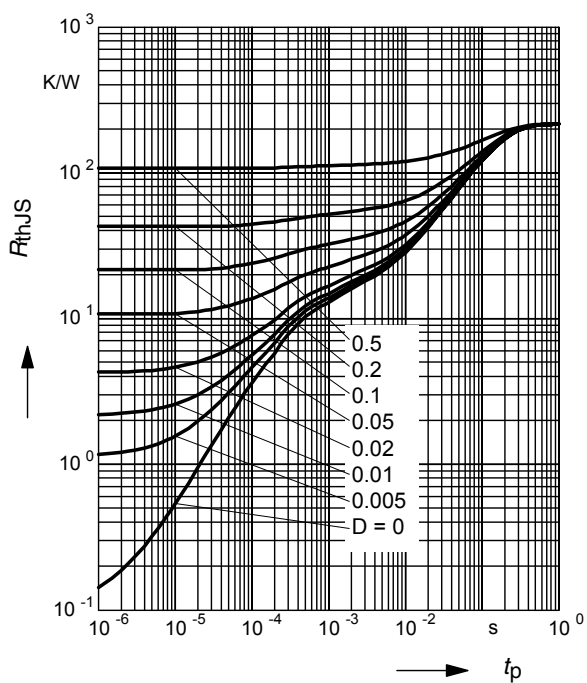
$V_{CE} = 5V$ (common emitter configuration)



Total power dissipation $P_{\text{tot}} = f(T_S)$



Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



Permissible Pulse Load

$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$

